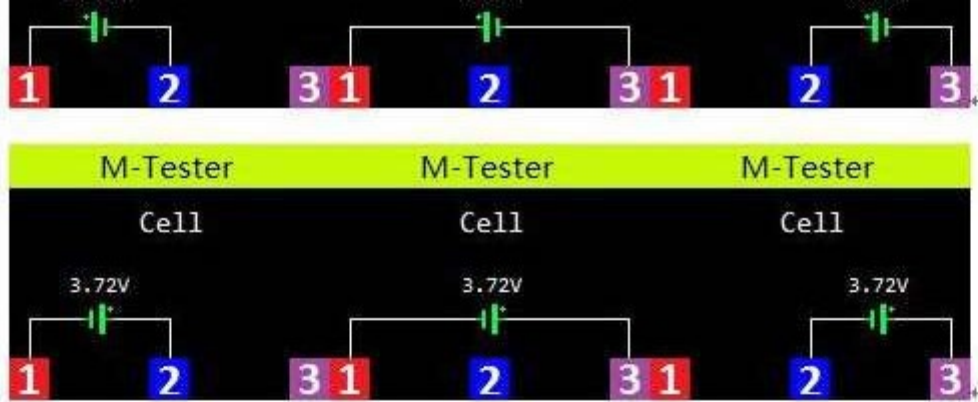




BJT(Bipolar Junction Transistor)↵



The main performance parameters are as follows:

Component↵	Range↵	Parameter Description↵
BJT↵	↵	hFE(DC Current Gain), Ube(Base-Emitter Voltage), Ic(Collector Current), Iceo(Collector Cut-off Current (IB=0)), Ices(Collector short Current), Uf(Forward Voltage of protecting diode) ⑤↵
Diode↵	Forward Voltage <4.50V↵	Forward Voltage, Diode Capacitance, Ir(Reverse Current) ②↵
Double Diodes↵		Forward Voltage↵
Zener Diode↵	0.01-4.50V↵ (Transistor test area)↵	Forward Voltage, Reverse Voltage↵
	0.01-30V↵ (Zener Diode test area)↵	Reverse Voltage↵
MOSFET↵	JFET↵	Cg(Gate Capacitance), Id(Drain Current) at Vgs(Gate to Source Threshold Voltag), Uf(Forward Voltage of protecting diode) ④↵
	IGBT↵	Id(Drain Current) at Vgs(Gate to Source Threshold Voltag), Uf(Forward Voltage of protecting diode) ④↵
	MOSFET↵	Vt(Gate to Source Threshold Voltag), Cg(Gate Capacitance), Rds(Drain to Source On Resistance), Uf(Forward Voltage of protecting diode) ④↵
Thyristor↵	Igt(Gate trigger	Gate trigger voltage↵